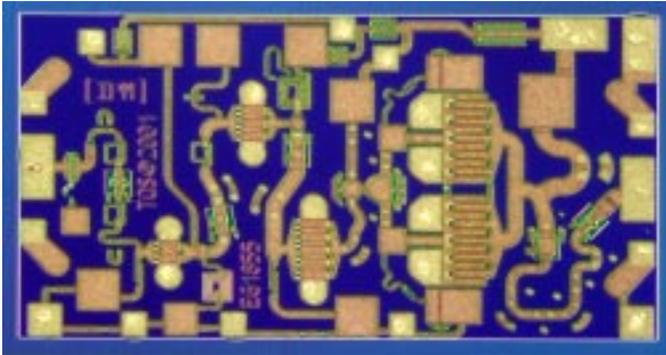


**12-19 GHz VSAT Amplifier**

**TGA2508-EPU**

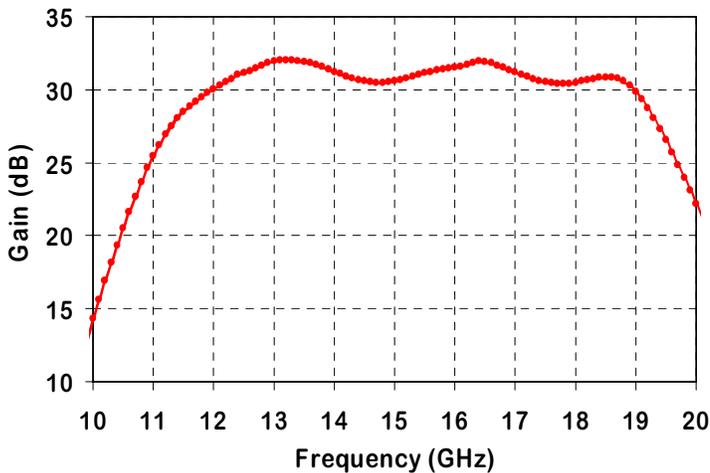


**Key Features**

- 0.50 um pHEMT Technology
- 30 dB Nominal Gain
- 30 dBm P1dB @ 15 GHz
- Bias Conditions: 7 V, 433 mA
- Chip Dimensions: 2.1 x 1.1 x 0.1 mm

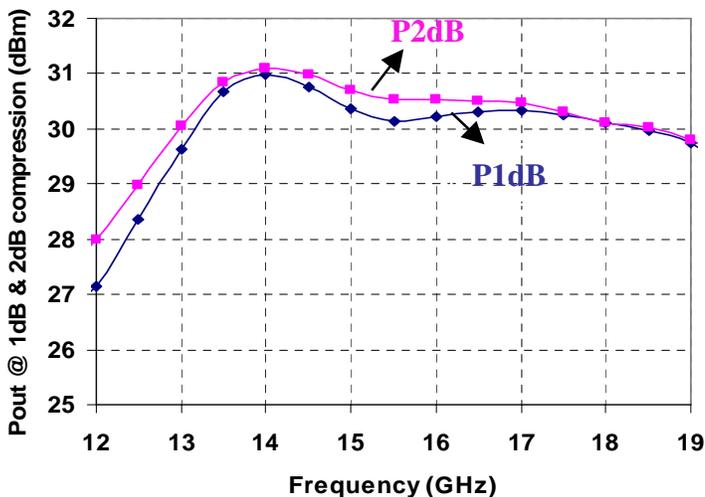
**Preliminary Measured Data**

Bias Conditions:  $V_d = 7\text{ V}$ ,  $I_d = 433\text{ mA}$



**Primary Applications**

- VSAT Ground Terminals
- Point to Point Radio
- Military Ku Band



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

**TABLE I**  
**MAXIMUM RATINGS 5/**

<b>SYMBOL</b>	<b>PARAMETER</b>	<b>VALUE</b>	<b>NOTES</b>
V <sup>+</sup>	Positive Supply Voltage	8 V	<u>4/</u>
V <sup>-</sup>	Negative Supply Voltage Range	-2 to 0 V	
I <sup>+</sup>	Positive Supply Current (Quiescent)	591 mA	<u>4/</u>
I <sub>G</sub>	Gate Supply Current	16 mA	
P <sub>IN</sub>	Input Continuous Wave Power	17 dBm	
P <sub>D</sub>	Power Dissipation	6.75 W	<u>3/ 4/</u>
T <sub>CH</sub>	Operating Channel Temperature	150 °C	<u>1/ 2/</u>
T <sub>M</sub>	Mounting Temperature (30 Seconds)	320 °C	
T <sub>STG</sub>	Storage Temperature	-65 to 150 °C	

- 1/ These ratings apply to each individual FET.
- 2/ Junction operating temperature will directly affect the device median time to failure (T<sub>M</sub>). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.
- 3/ When operated at this bias condition with a base plate temperature of 70 °C, the median life is reduced from 6.4E+7 to 1E+6 hrs.
- 4/ Combinations of supply voltage, supply current, input power, and output power shall not exceed P<sub>D</sub>.
- 5/ These ratings represent the maximum operable values for this device.

*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice*

**TABLE II**  
**ELECTRICAL CHARACTERISTICS**

(Ta = 25°C ± 5°C)

PARAMETER	TYPICAL	UNITS
Drain Operating	7	V
Quiescent Current	433	mA
Small Signal Gain	30	dB
Input Return Loss (Linear Small Signal)	17	dB
Output Return Loss (Linear Small Signal)	7	dB
Output Power @ 1 dB Compression Gain @ 15GHz	30	dBm

**TABLE III**  
**THERMAL INFORMATION\***

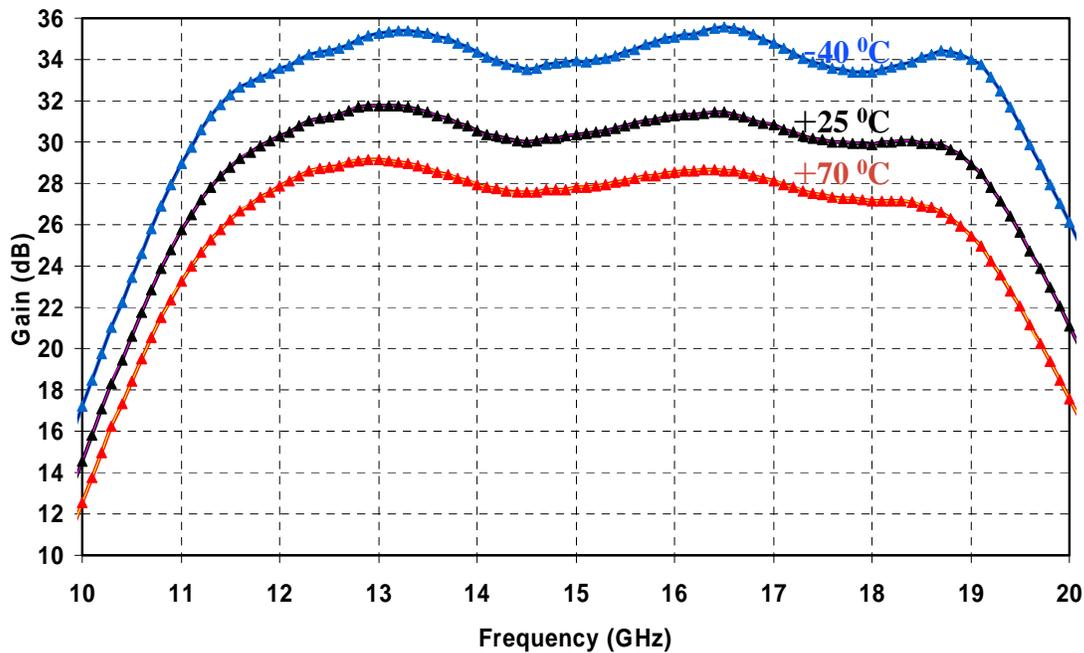
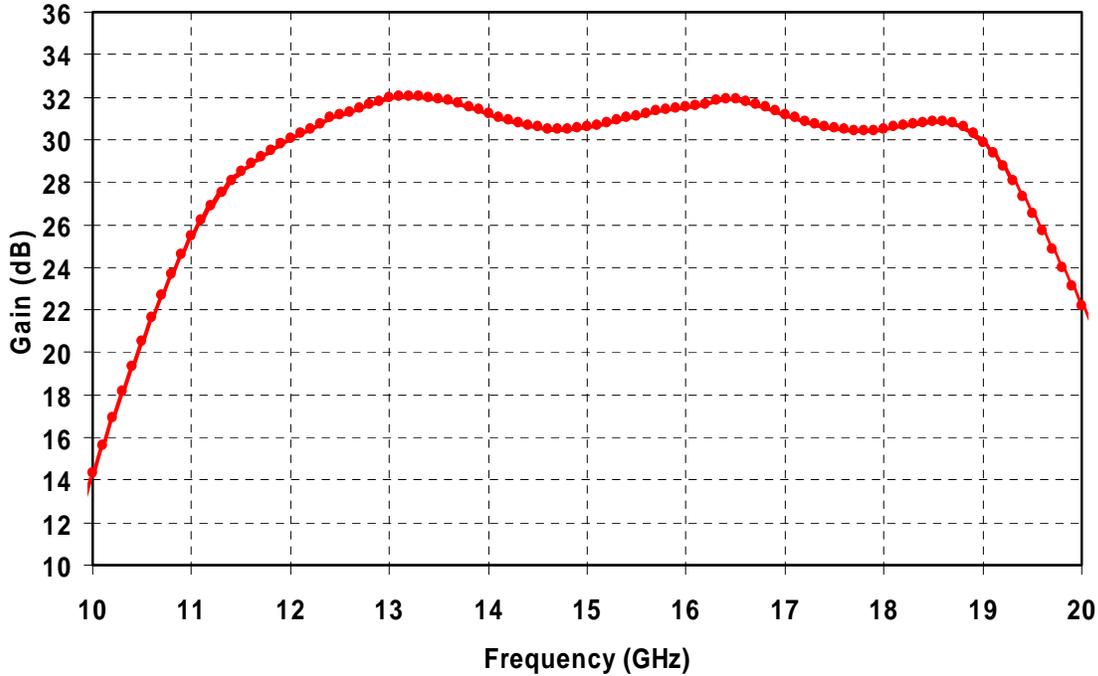
PARAMETER	TEST CONDITIONS	T <sub>CH</sub> (°C)	R <sub>θJC</sub> (°C/W)	T <sub>M</sub> (HRS)
R <sub>θJC</sub> Thermal Resistance (channel to backside of carrier)	Vd = 7 V I <sub>D</sub> = 433 mA P <sub>diss</sub> = 3.031 W	105.92	11.85	6.4E+7

Note: Assumes eutectic attach using 1.5 mil 80/20 AuSn mounted to a 20 mil CuMo Carrier at 70°C baseplate temperature. Worst case condition with no RF applied, 100% of DC power is dissipated.

\* This information is a result of a thermal model.

**Preliminary Measured Data**

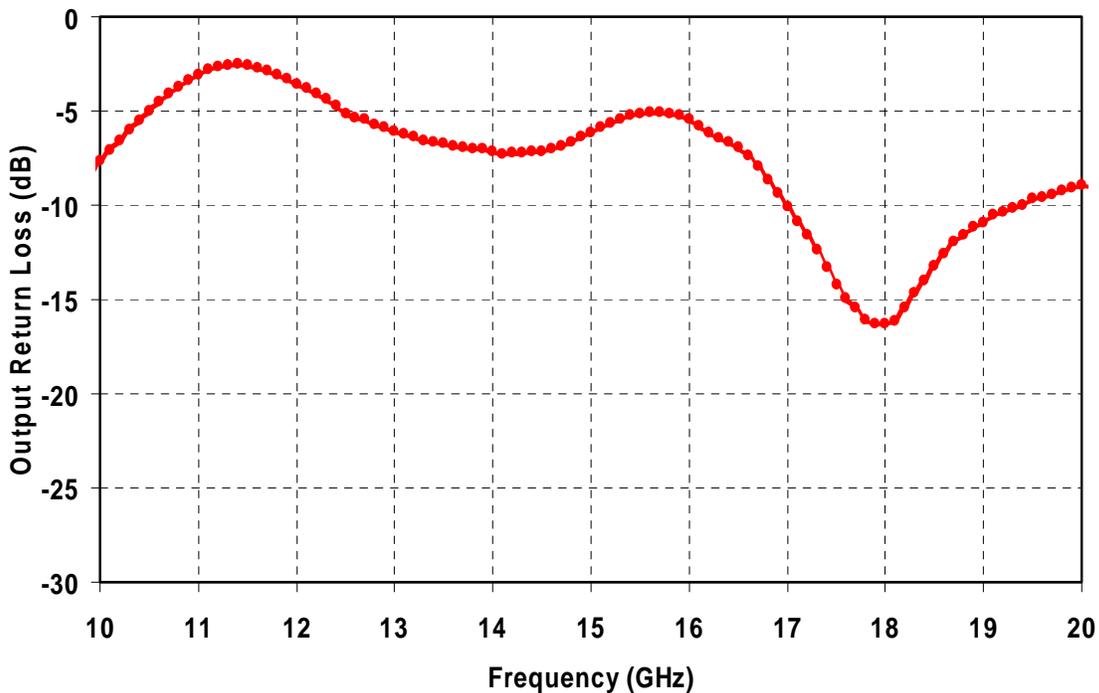
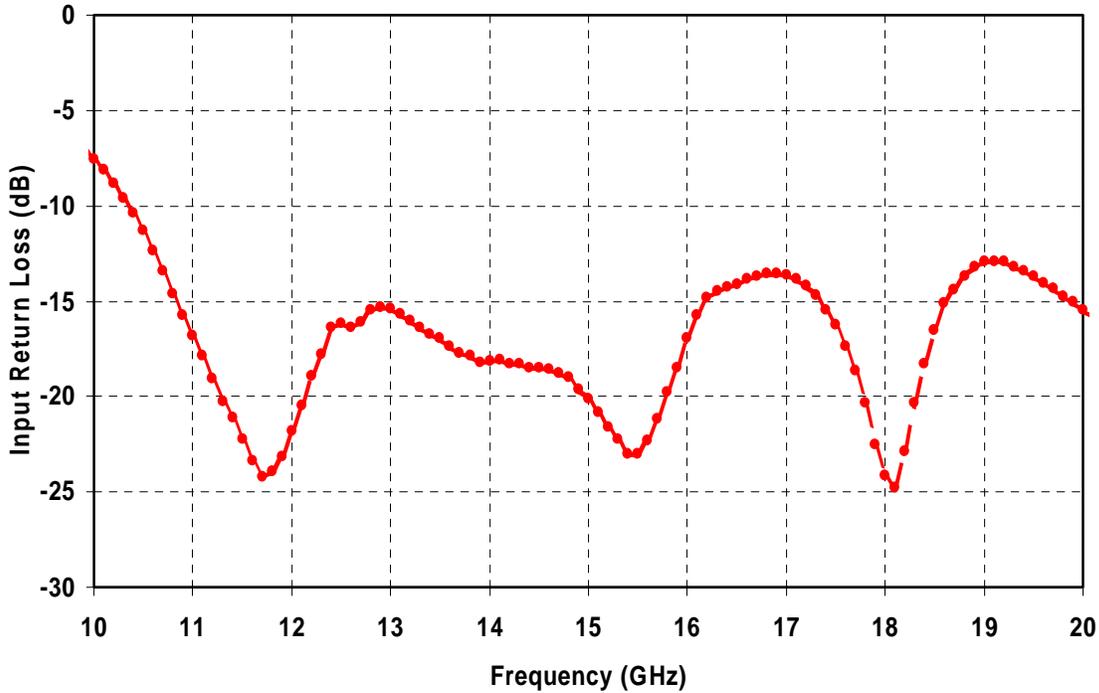
Bias Conditions:  $V_d = 7\text{ V}$ ,  $I_d = 433\text{ mA}$



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

### Preliminary Measured Data

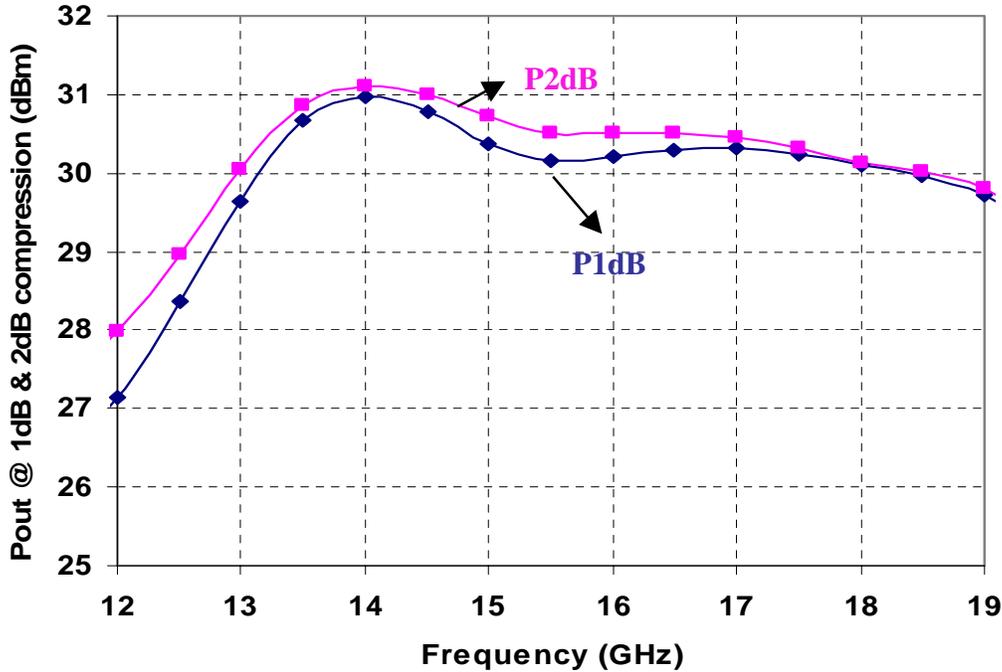
Bias Conditions:  $V_d = 7\text{ V}$ ,  $I_d = 433\text{ mA}$



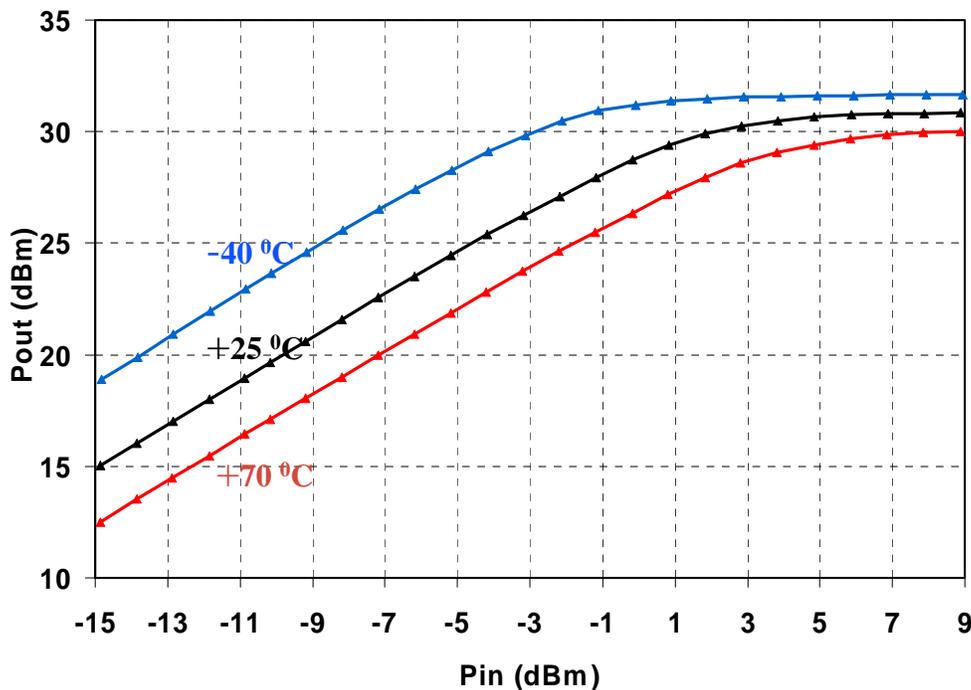
Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

**Preliminary Measured Data**

Bias Conditions:  $V_d = 7\text{ V}$ ,  $I_d = 433\text{ mA}$



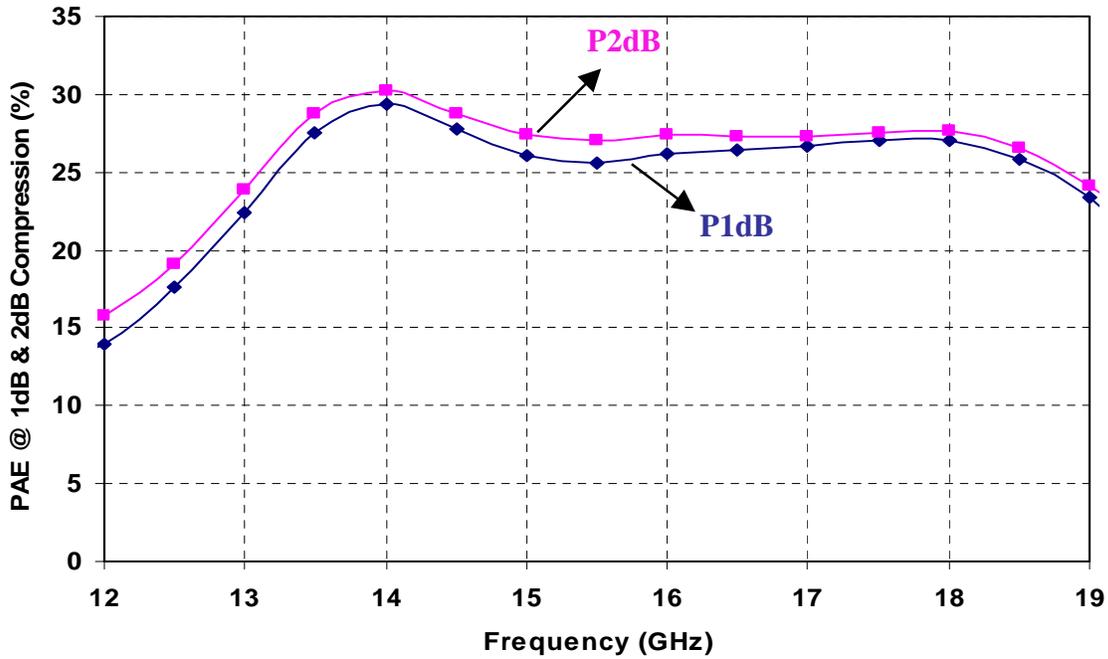
**Frequency @ 15 GHz**



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

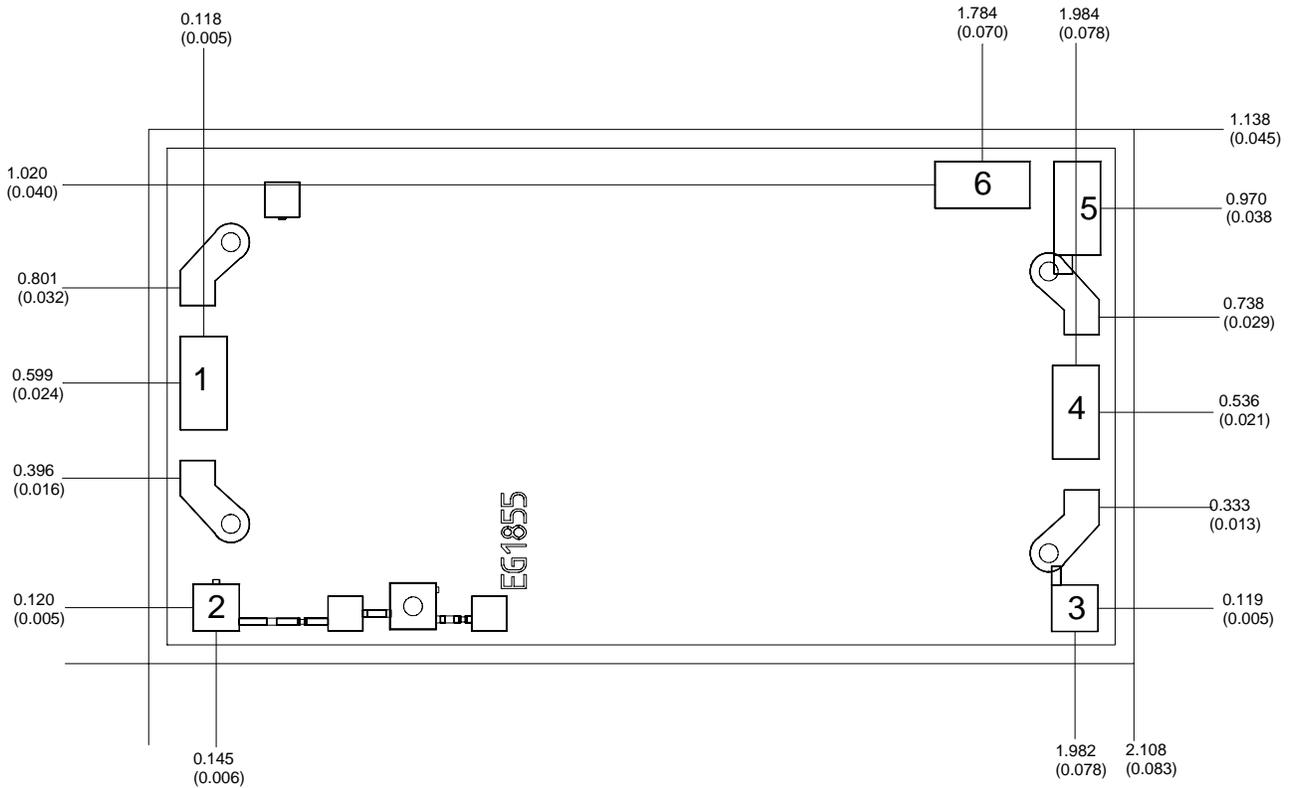
### Preliminary Measured Data

Bias Conditions:  $V_d = 7\text{ V}$ ,  $I_d = 433\text{ mA}$



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

**Mechanical Drawing**



Units: millimeters (inches)

Thickness: 0.100 (0.004)

Chip edge to bond pad dimensions are shown to center of bond pad

Chip size tolerance: +/- 0.051 (0.002)

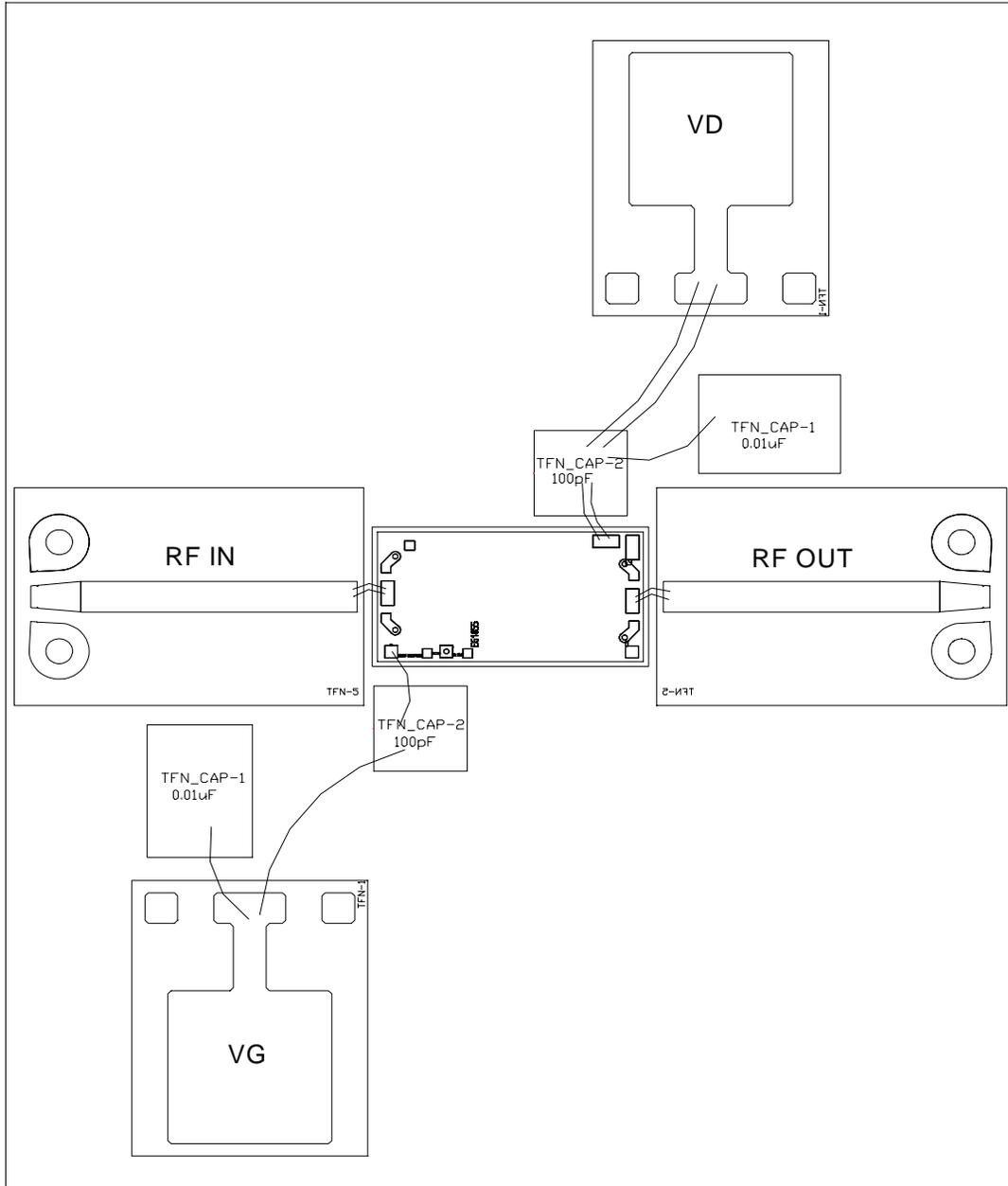
Bond pad #1:	(RF In)	0.098 x 0.199	(0.004 x 0.008)
Bond pad #2:	(Vg)	0.099 x 0.099	(0.004 x 0.004)
Bond pad #3:	(DC GND)*	0.098 x 0.099	(0.004 x 0.004)
Bond pad #4:	(RF Out)	0.099 x 0.198	(0.004 x 0.008)
Bond pad #5:	(DC GND)*	0.098 x 0.198	(0.004 x 0.008)
Bond pad #6:	(Vd)	0.202 x 0.098	(0.008 x 0.004)

\* Note: RF GND is back side of MMIC.

**GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.**

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**Chip Assembly Diagram**



**GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.**

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## **Assembly Process Notes**

Reflow process assembly notes:

- Use AuSn (80/20) solder with limited exposure to temperatures at or above 300°C.
- An alloy station or conveyor furnace with reducing atmosphere should be used.
- No fluxes should be utilized.
- Coefficient of thermal expansion matching is critical for long-term reliability.
- Devices must be stored in a dry nitrogen atmosphere.

Component placement and adhesive attachment assembly notes:

- Vacuum pencils and/or vacuum collets are the preferred method of pick up.
- Air bridges must be avoided during placement.
- The force impact is critical during auto placement.
- Organic attachment can be used in low-power applications.
- Curing should be done in a convection oven; proper exhaust is a safety concern.
- Microwave or radiant curing should not be used because of differential heating.
- Coefficient of thermal expansion matching is critical.

Interconnect process assembly notes:

- Thermosonic ball bonding is the preferred interconnect technique.
- Force, time, and ultrasonics are critical parameters.
- Aluminum wire should not be used.
- Discrete FET devices with small pad sizes should be bonded with 0.0007-inch wire.
- Maximum stage temperature is 200°C.

***GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.***

*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice*